

The documentation and process conversion measures necessary to comply with this revision shall be completed by 12 October 2004.

INCH-POUND

MIL-PRF-19500/687A  
 12 July 2004  
 SUPERSEDING  
 MIL-PRF-19500/687  
 14 March 2001

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, FIELD EFFECT RADIATION HARDENED (TOTAL DOSE AND SINGLE EVENT EFFECTS) TRANSISTOR, N-CHANNEL SILICON, TYPES 2N7509, 2N7510, AND 2N7511, JANTXVD, R AND JANSJ, R

This specification is approved for use by all Departments and Agencies of the Department of Defense.

\* The requirements for acquiring the product described herein shall consist of this specification sheet and MIL-PRF-19500.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for a N-channel, enhancement-mode, MOSFET, radiation hardened (total dose and single event effects (SEE) characterization), power transistor intended for use in high density power switching applications. Two levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1, (TO-254).

\* 1.3 Maximum ratings.  $T_A = +25^\circ\text{C}$ , unless otherwise specified.

Type	$P_T$ (1) $T_C = +25^\circ\text{C}$	$V_{DS}$	$V_{DG}$	$V_{GS}$	$I_{D1}$ (2) (3) $T_C = +25^\circ\text{C}$	$I_{D2}$ (2) (3) $T_C = +100^\circ\text{C}$	$I_S$	$I_{DM}$	$T_J$ and $T_{STG}$	$V_{ISO}$ 70,000 ft. altitude
	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A (pk)</u>	<u>°C</u>	<u>V dc</u>
2N7509	192	100	100	+30	70	55	70	200	-55	N/A
2N7510	192	200	200	+30	53	34	53	200	to	N/A
2N7511	192	250	250	+30	42	27	42	160	+150	250

(1) Derate linearly 1.54 W/°C for  $T_C > +25^\circ\text{C}$ .

(2) The following formula derives the maximum theoretical  $I_D$  limit.  $I_D$  is limited by package and internal wires and may be limited by pin diameter:

$$I_D = \sqrt{\frac{T_{JM} - T_C}{(R_{\theta IC}) \times (R_{DS(on)} \text{ at } T_{JM})}}$$

(3) See figure 2, maximum drain current graph.

\* Comments, suggestions, or questions on this document should be addressed to Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to [Semiconductor@dsc.dla.mil](mailto:Semiconductor@dsc.dla.mil). Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <http://www.dodssp.daps.mil/>.

1.4 Primary electrical characteristics at  $T_C = +25^\circ\text{C}$ .

Type	Min $V_{(BR)DSS}$ $V_{GS} = 0$ $I_D = 1.0 \text{ mA}$ dc	$V_{GS(TH)1}$ $V_{DS} = V_{GS}$ $I_D = 1.0 \text{ mA}$ dc	Max $I_{DSS1}$ $V_{GS} = 0$ $V_{GS} = 80\%$ of rated $V_{DS}$	Max $r_{DS(on)}$ (1) $V_{GS} = 12\text{V}$		$R_{\theta JC}$ max	$I_{AS}$	
				$T_J = 25^\circ\text{C}$ at $I_{D2}$	$T_J = 125^\circ\text{C}$ at $I_{D2}$			
	<u>V dc</u>	<u>V dc</u> Min    Max		<u><math>\mu\text{A dc}</math></u>	<u><math>\Omega</math></u>	<u><math>\Omega</math></u>	<u><math>^\circ\text{C/W}</math></u>	<u>A (pk)</u>
2N7509	100	2.0	4.5	25	0.0115	0.021	0.65	170
2N7510	200				0.034	0.065		110
2N7511	250				0.049	0.096		85

(1) Pulsed (see 4.5.1).

## 2. APPLICABLE DOCUMENTS

\* 2.1 General. The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

2.2 Government documents.

\* 2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

## \* DEPARTMENT OF DEFENSE SPECIFICATIONS

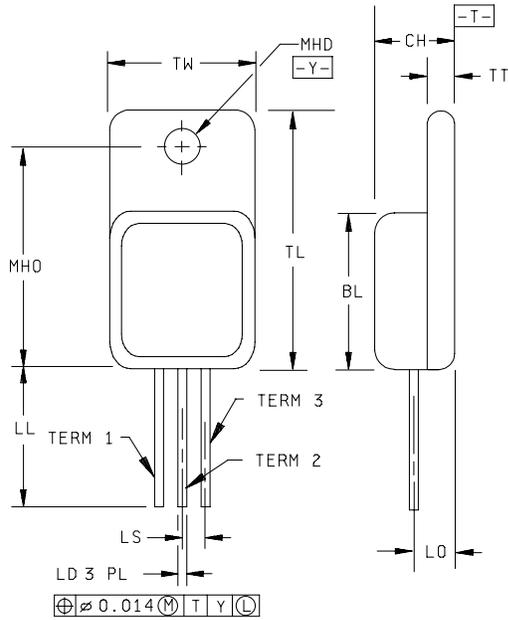
MIL-PRF-19500 - Semiconductor Devices, General Specification for.

## \* DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.

\* (Copies of these documents are available online at <http://assist.daps.dla.mil/quicksearch/> or <http://www.dodssp.daps.mil/> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.



Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.535	.545	13.59	13.84
CH	.249	.260	6.32	6.60
LD	.035	.045	0.89	1.14
LL	.52	.560	13.21	14.22
LO	.150 BSC		3.81 BSC	
LS	.150 BSC		3.81 BSC	
MHD	.139	.149	3.53	3.78
MHO	.665	.685	16.89	17.40
TL	.790	.800	20.07	20.32
TT	.040	.050	1.02	1.27
TW	.535	.545	13.59	13.84
Term 1	Drain			
Term 2	Source			
Term 3	Gate			

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. All terminals are isolated from case.
4. Die to base is BeO isolated, terminals to case ceramic (AL<sub>2</sub>O<sub>3</sub>) isolated.
5. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.

\* FIGURE 1. Physical dimensions for TO-254.

3. REQUIREMENTS

\* 3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.2 and 6.3).

\* 3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500 and as follows.

$I_{AS}$ .....Rated avalanche current, non-repetitive.

nC.....nano coulomb.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500, and figure 1 (TO-254AA) herein. Methods used for electrical isolation of the terminals shall employ materials that contain a minimum of 90 percent  $Al_2O_3$  (ceramic).

3.4.1 Lead finish. Unless otherwise specified, lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

\* 3.5 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in paragraph 1.3, 1.4, and table I.

\* 3.7 Electrical test requirements. The electrical test requirements shall be as specified in table I.

3.8 Electrostatic discharge protection. The devices covered by this specification require electrostatic discharge protection.

3.8.1 Handling. MOS devices must be handled with certain precautions to avoid damage due to the accumulation of static charge. However, the following handling practices are recommended.

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source,  $R \leq$  or 100 k ohms, whenever bias voltage is applied drain to source.

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- \* c. Conformance inspection (see 4.4 and tables I and II).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for qualification inspection in accordance with MIL-PRF-19500.

\* 4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table III tests, the tests specified in table III herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

MIL-PRF-19500/687A

\* 4.3 Screening. Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500) (1) (2)	Measurement	
	JANS	JANTXV
(3)	Gate stress test (see 4.3.1)	Gate stress test (see 4.3.1)
(3)	Method 3470 of MIL-STD-750, (see 4.3.2)	Method 3470 of MIL-STD-750, (see 4.3.2)
(3) 3c	Method 3161 of MIL-STD-750, (see 4.3.3)	Method 3161 of MIL-STD-750, (see 4.3.3)
7	Optional.	Optional.
9	$I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ subgroup 2 of table I herein	$I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ subgroup 2 of table I herein
10	Method 1042 of MIL-STD-750, test condition B	Method 1042 of MIL-STD-750, test condition B
11	$I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ , $r_{DS(ON)1}$ , $V_{GS(TH)1}$ Subgroup 2 of table I herein. $\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater.	$I_{GSSF1}$ , $I_{GSSR1}$ , $I_{DSS1}$ , $r_{DS(ON)1}$ , $V_{GS(TH)1}$ Subgroup 2 of table I herein.
12	Method 1042 of MIL-STD-750, test condition A, 240 hours minimum.	Method 1042 of MIL-STD-750, test condition A, 160 hours minimum.
13	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta r_{DS(ON)1} = \pm 20$ percent of initial value. $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value.	Subgroup 2 of table I herein $\Delta I_{GSSF1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 25$ $\mu$ A dc or $\pm 100$ percent of initial value, whichever is greater. $\Delta r_{DS(ON)1} = \pm 20$ percent of initial value. $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value.
14	Required.	Required.

- (1) At the end of the test program,  $I_{GSSF1}$ ,  $I_{GSSR1}$ , and  $I_{DSS1}$  are measured.
- (2) An out-of-family program to characterize  $I_{GSSF1}$ ,  $I_{GSSR1}$ ,  $I_{DSS1}$ , and  $V_{GS(th)1}$  shall be invoked.
- (3) Shall be performed anytime before screen 9.

\* 4.3.1 Gate stress test. Apply  $V_{GS} = 45$  V minimum for  $t = 250$   $\mu$ s minimum.

\* 4.3.2 Single pulse avalanche energy ( $E_{AS}$ ).

a.  $I_{AS}$  shall be as specified in 1.4 herein.

b.  $L = 0.1$  mH.

c. Gate to source resistor ( $25$  ohms  $\leq R_{GS} \leq 200$  ohms).

d.  $E_{AS} = 1/2 LI_{AS}^2$ .

e.  $V_{DD} = 50$  V to  $150$  V dc.

f. Initial junction temperature =  $+25^{\circ}\text{C}$ ,  $-5^{\circ}\text{C}$ ,  $+10^{\circ}\text{C}$ .

\* 4.3.3 Thermal impedance ( $V_{SD}$  measurement). The delta  $V_{SD}$  measurement shall be performed in accordance with method 3161 of MIL-STD-750. The delta  $V_{SD}$  conditions ( $I_H$  and  $V_H$ ) and maximum limit shall be derived by each vendor from the thermal response curves (see figure 3) and shall be specified in the certificate of conformance prior to qualification. The following parameter measurements shall apply:

a. Measuring current ( $I_M$ )..... 10 mA.

b. Heating time ( $t_H$ )..... 100 ms.

c. Measurement time delay ( $t_{MD}$ )..... 30 - 60  $\mu$ s.

d. Sample window time ( $t_{SW}$ )..... 10  $\mu$ s maximum.

4.4 Conformance. Conformance inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for conformance inspection in accordance with MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table V of MIL-PRF-19500 and table I herein.

\* 4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VIa (JANS) and in table VIb (JANTXV) of MIL-PRF-19500, and 4.4.2.1 and 4.4.2.2 herein. Electrical measurements (end-points) shall be in accordance with table 1, subgroup 2 herein. Delta  $V_{SD}$  measurements shall be in accordance with table IV herein.

MIL-PRF-19500/687A

4.4.2.1 Group B inspection, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1051	Test condition F or G, 100 cycles.
B4	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.
B5	1042	Accelerated steady-state reverse bias, condition A.
B5	1042	Accelerated steady-state gate bias, condition B.
B6	3161	Thermal resistance, see 4.5.2.

4.4.2.2 Group B inspection, table VIb (JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1042	Intermittent operation life, condition D, 2,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.
B5	3161	Thermal resistance, see 4.5.2.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table IV herein.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Terminal strength, test condition A, weight = 10 pounds, $t = 15$ seconds.
C5	3161	See 4.5.2.
C6	1042	Intermittent operation life, condition D, 6,000 cycles. No heat sink or forced-air cooling on the device shall be permitted during the on cycle. $t_{on} = 30$ seconds minimum.

\* 4.4.4 Group D inspection. Group D inspection shall be conducted in accordance with table VIII of MIL-PRF-19500 and table II herein.

4.4.4.1 Design parameters. Not tested on a per lot basis. Design shall be such that the devices shall be capable of meeting the requirements in SEE safe operating area graphs.

\* 4.4.5 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table IX of MIL-PRF-19500 and as specified in table III herein. Electrical measurements (end points) and delta requirements shall be in accordance with the applicable steps of table IV herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Thermal resistance. Thermal resistance measurements shall be performed in accordance with method 3161 of MIL-STD-750. The maximum limit of  $R_{\theta JC} = 0.65^{\circ}\text{C}/\text{W}$ . The following parameters shall apply:

- a. Measuring current ( $I_M$ )..... 10 mA.
- b. Drain heating current ( $I_H$ )..... 4 A.
- c. Heating time ( $t_H$ )..... Steady-state (see method 3161 of MIL-STD-750).
- d. Drain-source heating voltage ( $V_H$ )..... 25 V.
- e. Measurement time delay ( $t_{MD}$ )..... 30 to 60  $\mu\text{s}$ .
- f. Sample window time ( $t_{SW}$ )..... 10  $\mu\text{s}$  maximum.

MIL-PRF-19500/687A

\* TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Units
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Breakdown voltage drain to source 2N7509 2N7510 2N7511	3407	$V_{GS} = 0V$ , $I_D = 1 \text{ mA dc}$ , bias condition C	$V_{(BR)DSS}$	100 200 250		V dc V dc V dc
Gate to source voltage (threshold)	3403	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA dc}$	$V_{GS(TH)1}$	2.0	4.5	V dc
Gate current	3411	$V_{GS} = +30V \text{ dc}$ , bias condition C, $V_{DS} = 0V$	$I_{GSSF1}$		+100	nA dc
Gate current	3411	$V_{GS} = -30V \text{ dc}$ , bias condition C, $V_{DS} = 0V$	$I_{GSSR1}$		-100	nA dc
Drain current	3413	$V_{GS} = 0V \text{ dc}$ , bias condition C, $V_{DS} = 80 \text{ percent of rated } V_{DS}$	$I_{DSS1}$		25	$\mu\text{A dc}$
Static drain to source on-state resistance 2N7509 2N7510 2N7511	3421	$V_{GS} = 12V \text{ dc}$ , condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)1}$		0.0115 0.034 0.049	$\Omega$ $\Omega$ $\Omega$
Static drain to source on-state voltage 2N7509 2N7510 2N7511	3405	$V_{GS} = 12V \text{ dc}$ , condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	$V_{DS(ON)}$		0.84 1.91 2.18	V dc V dc V dc
Forward voltage	4011	$V_{GS} = 0V \text{ dc}$ , condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	$V_{SD}$		1.2	V dc

See footnote at end of table.

\* TABLE I. Group A inspection - Continued.

Inspection <u>1</u> /	MIL-STD-750		Symbol	Limits		Units
	Method	Conditions		Min	Max	
<u>Subgroup 3</u>						
High temperature operation		$T_C = T_J = +125^\circ\text{C}$				
Gate current	3411	$V_{GS} = \pm 30\text{V dc}$ , bias condition C, $V_{DS} = 0\text{V}$	$I_{GSS2}$		$\pm 200$	nA dc
Drain current	3413	$V_{GS} = 0\text{V dc}$ , bias condition C, $V_{DS} = 80$ percent of rated $V_{DS}$	$I_{DSS2}$		0.250	mA dc
Static drain to source on-state resistance 2N7509 2N7510 2N7511	3421	$V_{GS} = 12\text{V dc}$ , condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)2}$		0.021 0.065 0.096	$\Omega$ $\Omega$ $\Omega$
Gate to source voltage (threshold)	3403	$V_{DS} = V_{GS}$ , $I_D = 1\text{ mA dc}$	$V_{GS(TH)2}$	1.0		V dc
Low temperature operation		$T_C = T_J = -55^\circ\text{C}$				
Gate to source voltage (threshold)	3403	$V_{DS} = V_{GS}$ , $I_D = 1\text{ mA dc}$	$V_{GS(TH)3}$		5.5	V dc
<u>Subgroup 4</u>						
Switching time test	3472	$I_D = I_{D1}$ , $V_{GS} = 12\text{ V dc}$ , $R_G = 2.35\ \Omega$ , $V_{DD} = 50$ percent of rated $V_{DS}$				
Turn-on delay time 2N7509 2N7510 2N7511			$t_{D(on)}$		35 35 35	ns ns ns
Rise time 2N7509 2N7510 2N7511			$t_R$		140 140 70	ns ns ns

See footnote at end of table.

\* TABLE I. Group A inspection – Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Units
	Method	Conditions		Min	Max	
<u>Subgroup 4 - Continued.</u>  Turn-off delay time  2N7509 2N7510 2N7511  Fall time  2N7509 2N7510 2N7511			$t_{D(off)}$    $t_f$		60 65 70   20 15 15	ns ns ns   ns ns ns
<u>Subgroup 5</u>  Safe operating area test (high voltage)  Electrical measurements	3474	See figure 4, $t_p = 10$ ms min. $V_{DS} = 80$ percent of max. rated $V_{DS}$ ( $V_{DS} \leq 200$ V)  See table I, subgroup 2				
<u>Subgroup 6</u>  Not applicable						
<u>Subgroup 7</u>  Gate charge  On-state gate charge  2N7509 2N7510 2N7511  Gate to source charge  2N7509 2N7510 2N7511	3471	Condition A or B	$Q_{G(ON)}$   $Q_{GS}$		150 115 115   45 60 45	nC nC nC   nC nC nC

See footnote at end of table.

\* TABLE I. Group A inspection – Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Units
	Method	Conditions		Min	Max	
<u>Subgroup 7</u> - Continued.						
Gate to drain charge			$Q_{GD}$			
2N7509					55	nC
2N7510					30	nC
2N7511					45	nC
Reverse recovery time	3473	$di/dt = 100 \text{ A}/\mu\text{s}, V_{DD} \leq 50 \text{ V},$ $I_D = I_{D1}$	$t_{rr}$			
2N7509					290	ns
2N7510					375	ns
2N7511					590	ns

1/ For sampling plan, see MIL-PRF-19500.

\* TABLE II. Group D inspection.

Inspection 1/ 2/ 3/ 4/ 5/	MIL-STD-750		Symbol	Pre-irradiation limits		Post irradiation limits		Units
	Method	Conditions		Min.	Max.	Min.	Max.	
<u>Subgroup 1</u>								
Not applicable								
<u>Subgroup 2</u>		$T_C = +25^\circ\text{C}$						
Steady state total dose irradiation ( $V_{GS}$ bias)	1019	$V_{GS} = 12\text{V}, V_{DS} = 0\text{V}$						
Steady state total dose irradiation ( $V_{DS}$ bias)	1019	$V_{GS} = 0\text{V}, V_{DS} = 80$ percent of rated $V_{DS}$						
Breakdown voltage drain to source	3407	$V_{GS} = 0\text{V}, I_D = 1$ mA dc, bias condition C	$V_{(BR)DSS}$					
2N7509				100		100		V dc
2N7510				200		200		V dc
2N7511				250		250		V dc
Gate to source voltage (threshold)	3403	$V_{DS} = V_{GS}, I_D = 1$ mA dc	$V_{GS(TH)1}$	2.0	4.5	2.0	4.5	V dc
Gate current	3411	$V_{GS} = \pm 30\text{V}$ dc, $V_{DS} = 0\text{V}$ , bias condition C	$I_{GSS1}$		$\pm 100$		$\pm 100$	nA dc
Drain current	3413	$V_{GS} = 0\text{V}, V_{DS} = 80$ percent of rated $V_{DS}$ , bias condition C	$I_{DSS1}$		25		25	$\mu\text{A}$ dc
Static drain to source on-state resistance	3421	$V_{GS} = 12\text{V}$ dc, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)1}$					
2N7509					0.0115		0.0115	$\Omega$
2N7510					0.034		0.034	$\Omega$
2N7511					0.049		0.049	$\Omega$
Static drain to source on-state voltage	3405	$V_{GS} = 12\text{V}$ dc, condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	$V_{DS(ON)}$					
2N7509					0.84		0.84	V dc
2N7510					1.91		1.91	V dc
2N7511					2.18		2.18	V dc

1/ For sampling plan see MIL-PRF-19500.

2/ Electrical specifications are for 'D' and 'R' rad levels.

3/ Group D qualification may be performed prior to lot formation. Wafers qualified to these group D QCI requirements may be used for any other specification sheet utilizing the same die design.

4/ Separate samples shall be pulled for each bias.

5/ At the manufacturer's option, group D samples need not be subjected to all the screening tests, but shall be assembled in its qualified package or in any qualified package that the manufacturer has data to correlate the performance to the designated package.

\* TABLE III. Group E inspection (all quality levels) for qualification or re-qualification only.

Inspection <u>1/ 2/ 3/ 4/ 5/</u>	MIL-STD-750		Qualification and large lot conformance inspection
	Method	Conditions	
<u>Subgroup 1</u>			12 devices c = 0
Temperature cycling (air to air)	1051	Test condition F or G, 500 cycles	
Hermetic seal	1071	Test conditions G or H	
Fine leak		Test conditions C or D	
Gross leak			
Electrical measurements		See table I, subgroup 2 and table IV, step 1	
<u>Subgroup 2 1/</u>			12 devices c = 0
Steady-state gate bias	1042	Test condition B; 1,000 hours	
Electrical measurements		See table I, subgroup 2 and table IV, step 1	
Steady state reverse bias	1042	Test condition A; 1,000 hours	
Electrical measurements		See table I, subgroup 2 and table IV, step 1	
<u>Subgroup 3</u>			3 devices, c = 0
DPA	2102		
<u>Subgroup 4</u>			sample size N/A
Thermal impedance curves		Each supplier shall submit their qual-lot average and design maximum thermal impedance curves. In addition, the optimal test conditions and $Z_{\theta JX}$ limit shall be provided to the qualifying activity in the qualification report	
<u>Subgroup 5</u>			15 devices c = 0
Barometric pressure test (not required for $V_{BR(DSS)} \leq 200$ V)	1001	Test condition C	
2N7511		$V_{DS} = 250$ V; $I_{(ISO)} < 0.25$ mA	
<u>Subgroup 6</u>			3 devices
ESD	1020	Not required for devices classified as ESD class 1.	

See footnotes at end of table.

\* TABLE III. Group E inspection (all quality levels) - for qualification or re-qualification only - Continued.

Inspection <u>1/ 2/ 3/ 4/ 5/</u>	MIL-STD-750		Qualification and large lot conformance inspection
	Method	Conditions	
<u>Subgroup 8</u>			3 devices <u>5/</u> c = 0
Electrical measurements <u>3/</u>		I <sub>GSSF1</sub> , I <sub>GSSR1</sub> , and I <sub>DSS1</sub> in accordance with table I, subgroup 2	
SEE testing <u>4/</u>	1080	See figure 5, fluence = 3e5 ±20 percent ions/cm <sup>2</sup> Flux = 5e3 to 2e4 ions/cm <sup>2</sup> sec Beam energy = 260 to 360 MeV Temperature = 25°C ±5°C	
2N7509		LET = 36 to 40 MeV-cm <sup>2</sup> /mg Ion range = 35 to 40 microns Insitu bias conditions: V <sub>DS</sub> = 100 V and V <sub>GS</sub> = -10 V	
		LET = 56 to 60 MeV-cm <sup>2</sup> /mg Ion range = 30 to 35 microns Insitu bias conditions: V <sub>DS</sub> = 100 V and V <sub>GS</sub> = -5 V V <sub>DS</sub> = 50 V and V <sub>GS</sub> = -8 V	
		LET = 80 to 84 MeV-cm <sup>2</sup> /mg Ion range = 25 to 30 microns Insitu bias conditions: V <sub>DS</sub> = 80 V and V <sub>GS</sub> = 0 V V <sub>DS</sub> = 50 V and V <sub>GS</sub> = -5 V	
2N7510		LET = 36 to 40 MeV-cm <sup>2</sup> /mg Ion range = 35 to 40 microns Insitu bias conditions: V <sub>DS</sub> = 200 V and V <sub>GS</sub> = -20 V	
		LET = 56 to 60 MeV-cm <sup>2</sup> /mg Ion range = 30 to 35 microns Insitu bias conditions: V <sub>DS</sub> = 200 V and V <sub>GS</sub> = -10 V	
		LET = 80 to 84 MeV-cm <sup>2</sup> /mg Ion range = 25 to 30 microns Insitu bias conditions: V <sub>DS</sub> = 160 V and V <sub>GS</sub> = -5 V V <sub>DS</sub> = 120 V and V <sub>GS</sub> = -10 V	

See footnotes at end of table.

\* TABLE III. Group E inspection (all quality levels) - for qualification or re-qualification only - Continued.

Inspection <u>1/</u> <u>2/</u> <u>3/</u> <u>4/</u> <u>5/</u>	MIL-STD-750		Qualification and large lot conformance inspection
	Method	Conditions	
<p><u>Subgroup 8</u>- continued</p> <p>2N7511</p> <p>Electrical measurements <u>3/</u></p> <p><u>Subgroup 9</u></p> <p>Commutating diode for safe operating area test procedure for measuring dv/dt during reverse recovery of power MOSFET transistors or insulated gate bipolar transistors</p>	3476	<p>LET = 36 to 40 MeV-cm<sup>2</sup>/mg Ion range = 35 to 40 microns Insitu bias conditions: V<sub>DS</sub> = 250 V and V<sub>GS</sub> = -20 V</p> <p>LET = 56 to 60 MeV-cm<sup>2</sup>/mg Ion range = 30 to 35 microns Insitu bias conditions: V<sub>DS</sub> = 250 V and V<sub>GS</sub> = -10 V</p> <p>LET = 80 to 84 MeV-cm<sup>2</sup>/mg Ion range = 25 to 30 microns Insitu bias conditions: V<sub>DS</sub> = 200 V and V<sub>GS</sub> = -5 V V<sub>DS</sub> = 150 V and V<sub>GS</sub> = -10 V</p> <p>I<sub>GSSF1</sub>, I<sub>GSSR1</sub>, and I<sub>DSS1</sub> in accordance with table I, subgroup 2</p>	<p>22 devices c = 0</p>

1/ A separate sample for each test may be pulled.

2/ Group E qualification of single event effect testing may be performed prior to lot formation. Wafers qualified to these group E QCI requirements may be used for any other specification utilizing the same die design.

3/ As a minimum, gate to source leakages and drain to source leakage are to be examined to verify the electrical performance of the DUT prior to and after test. At the manufacturer's option, the remaining static tests in table IV, with the exception of step 8, may be performed.

4/ Devices passing a given combination of drain and gate voltage for an LET of 80 to 84 MeV-cm<sup>2</sup>/mg qualify the same conditions for an LET of 56 to 60 MeV-cm<sup>2</sup>/mg or an LET of 36 to 40 MeV-cm<sup>2</sup>/mg.

5/ This sampling plan applies to each bias condition specified.

MIL-PRF-19500/687A

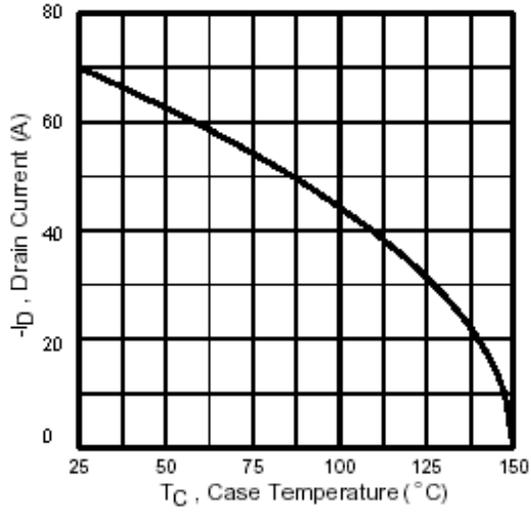
\* TABLE IV. Group A, B, C, and E delta measurements.

Step	Inspection <u>1/</u> <u>2/</u>	MIL-STD-750		Symbol	Limits		Units
		Method	Conditions		Min	Max	
1.	Thermal response	3161	See 4.3.3	$\Delta V_{SD}$		100	mV

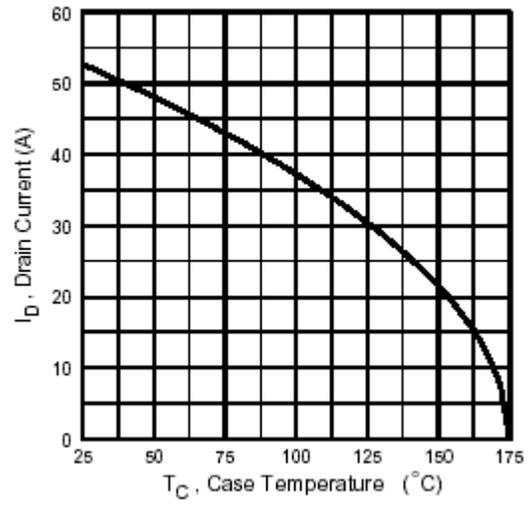
1/ The delta measurements for table VIa (JANS) of MIL-PRF-19500 are: Subgroup 4

2/ The delta measurements for table VII of MIL-PRF-19500 are: Subgroup 6.

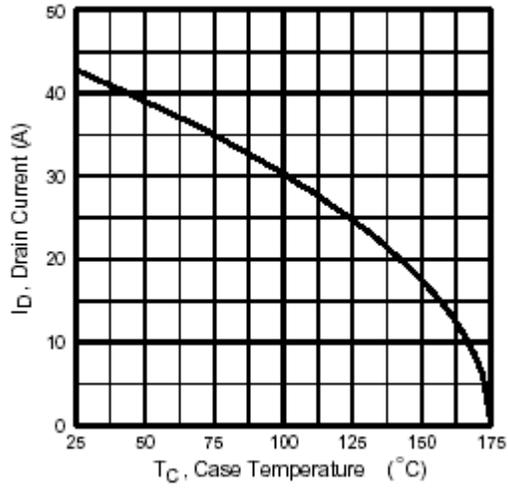
3/ The delta measurements for table IX of MIL-PRF-19500 are: Subgroups 1, 2, and 6.



2N7509

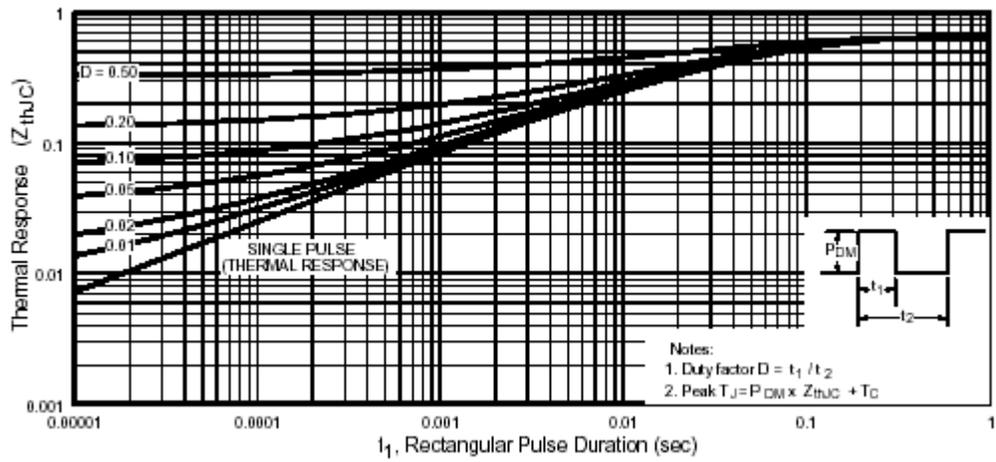


2N7510

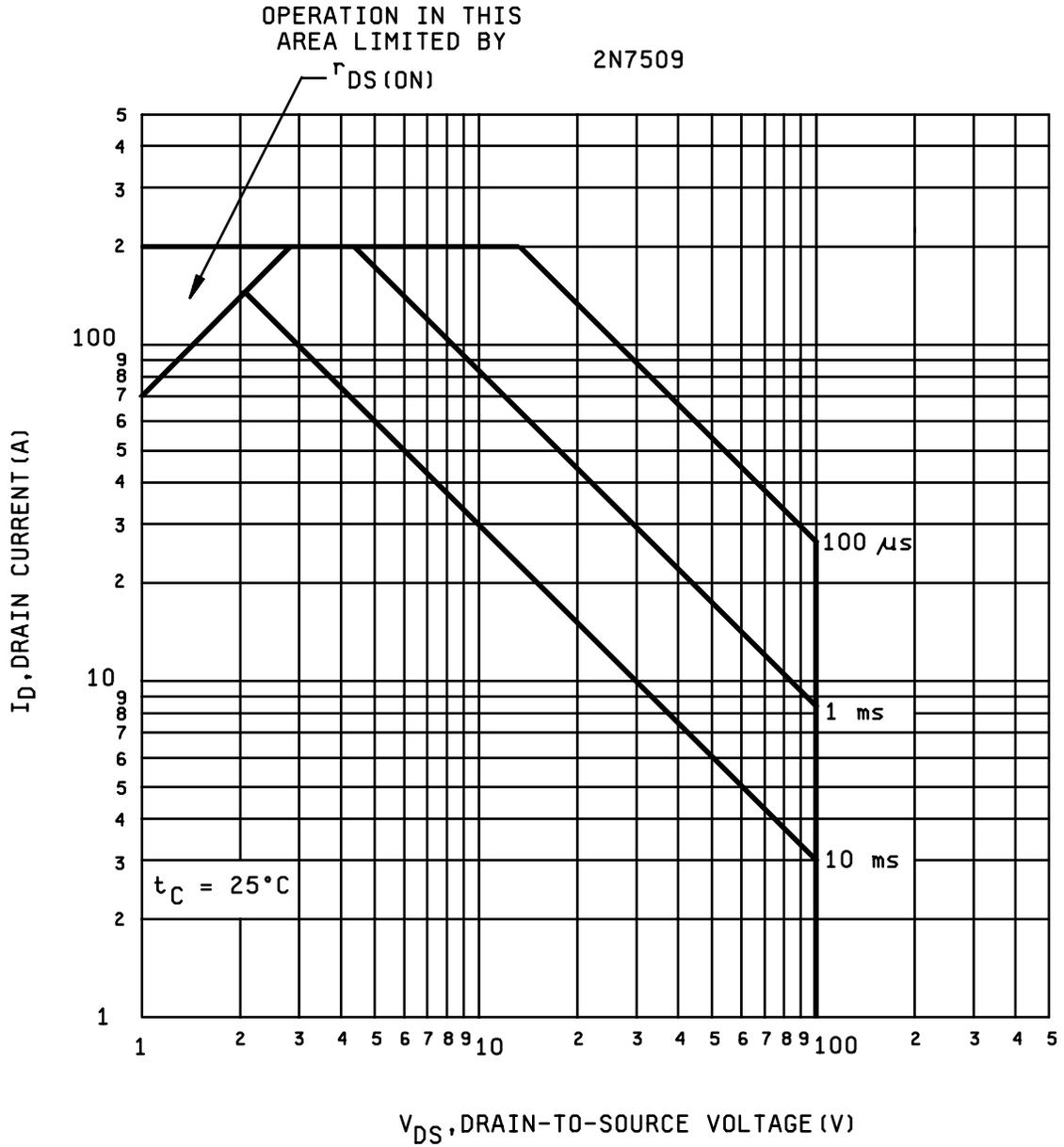


2N7511

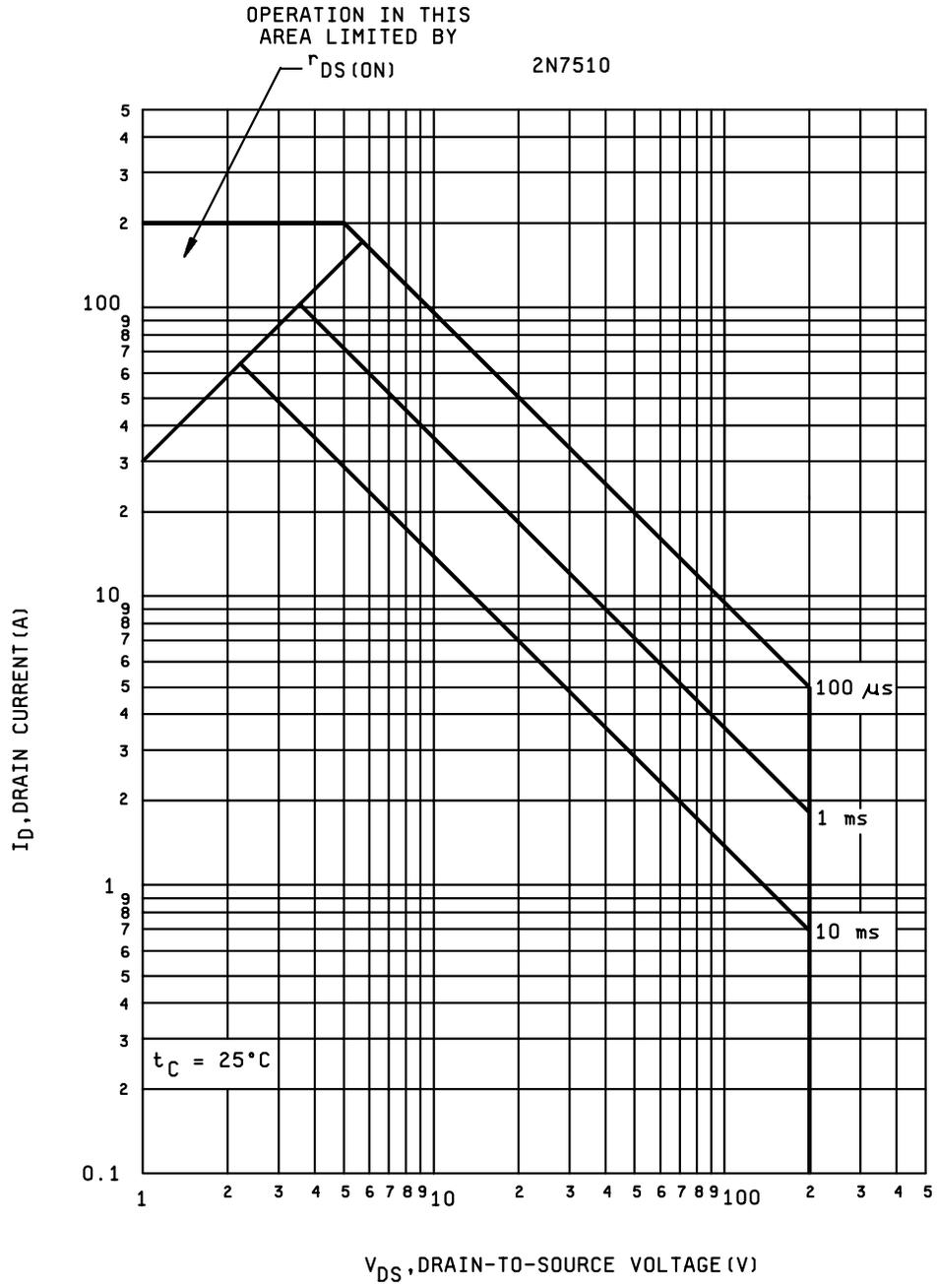
\* FIGURE 2. Maximum drain current vs case temperature graphs.



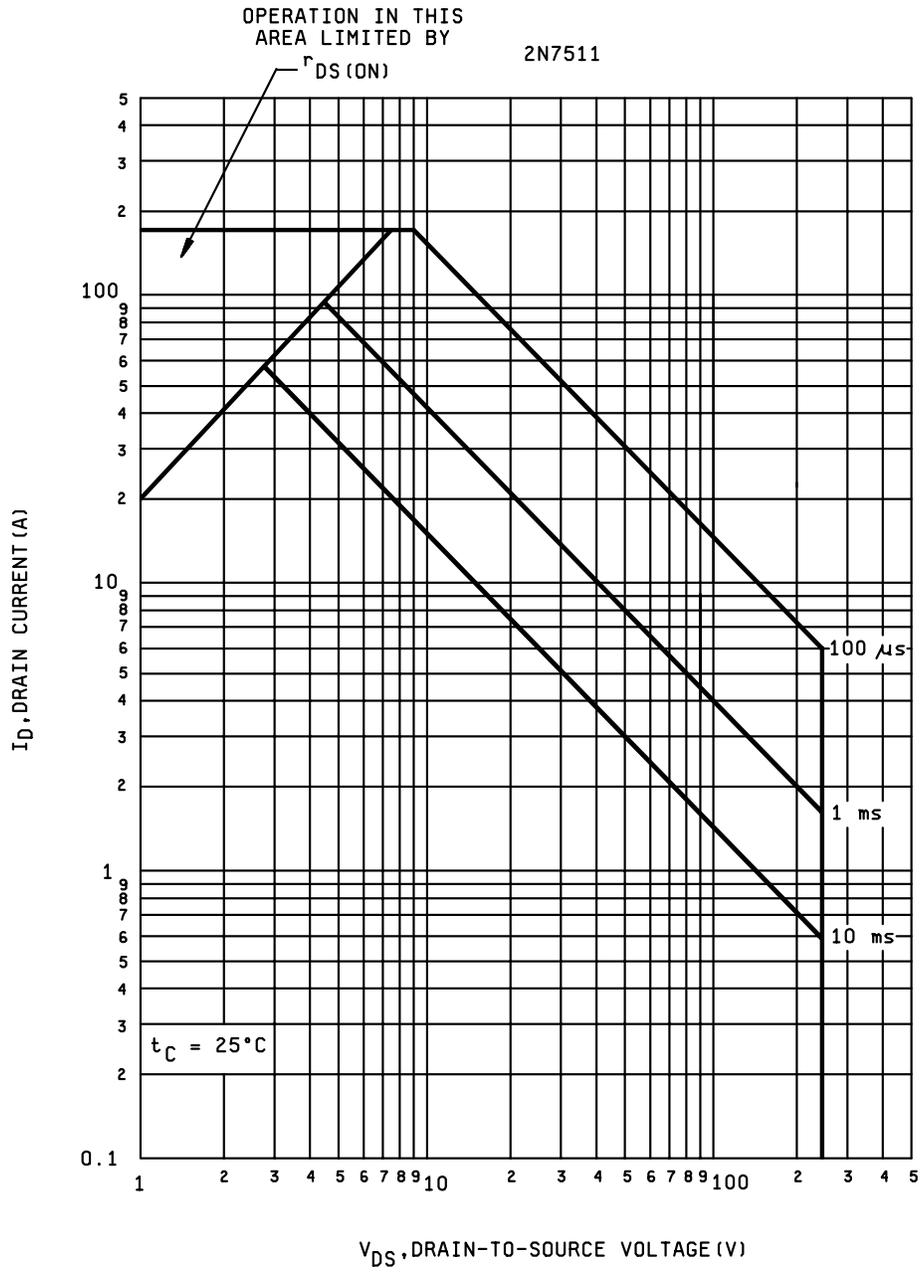
\* FIGURE 3. Thermal response curves.



\* FIGURE 4. Safe operating area graphs.

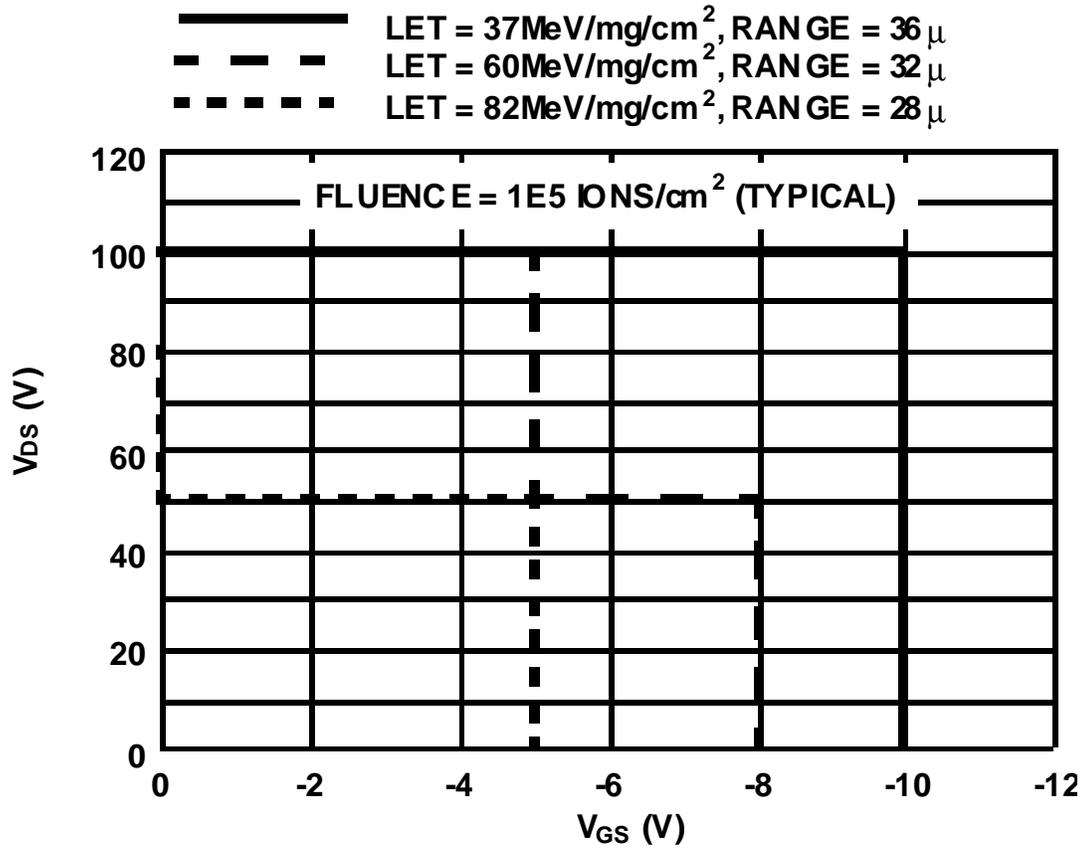


\* FIGURE 4. Safe operating area graphs -continued.

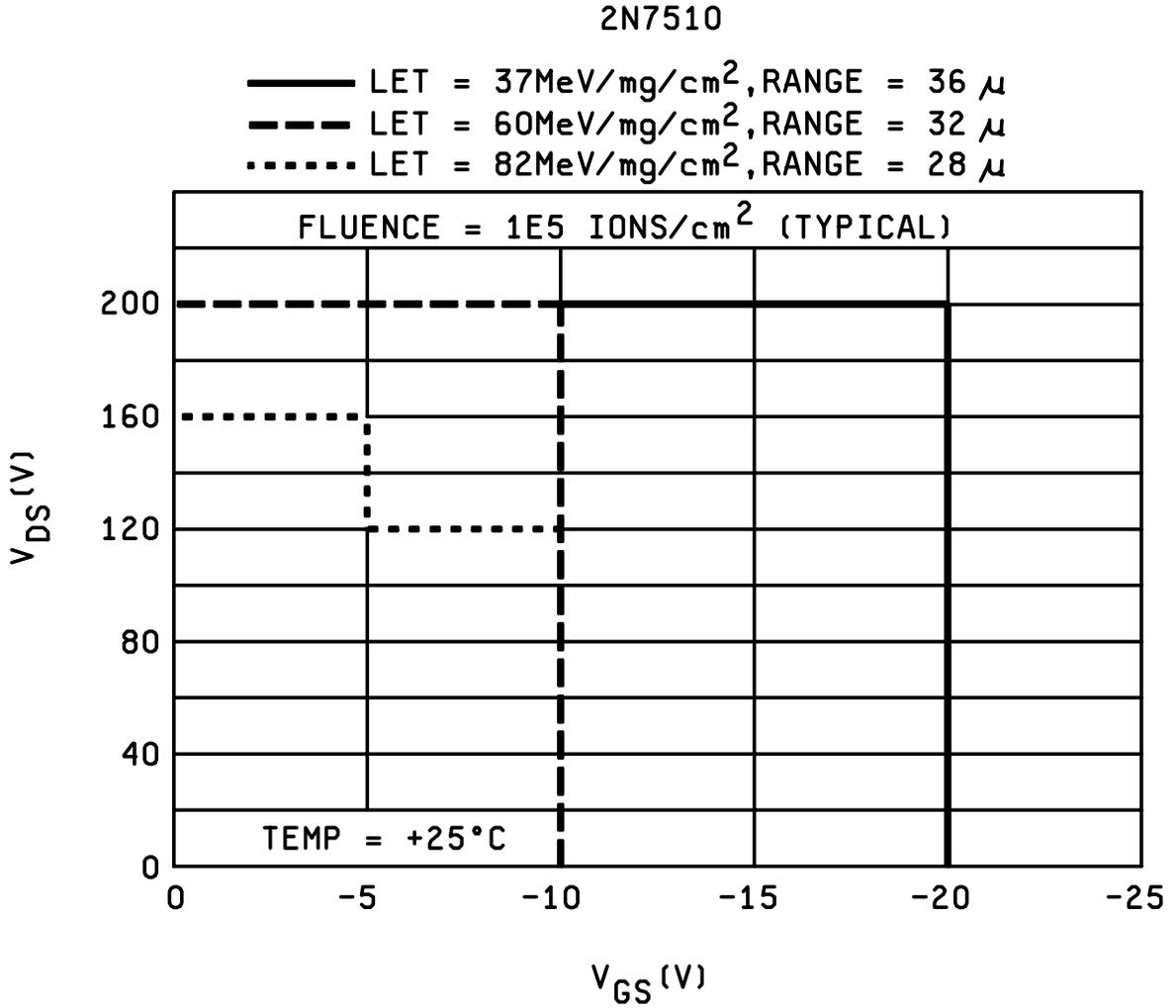


\* FIGURE 4. Safe operating area graphs – Continued.

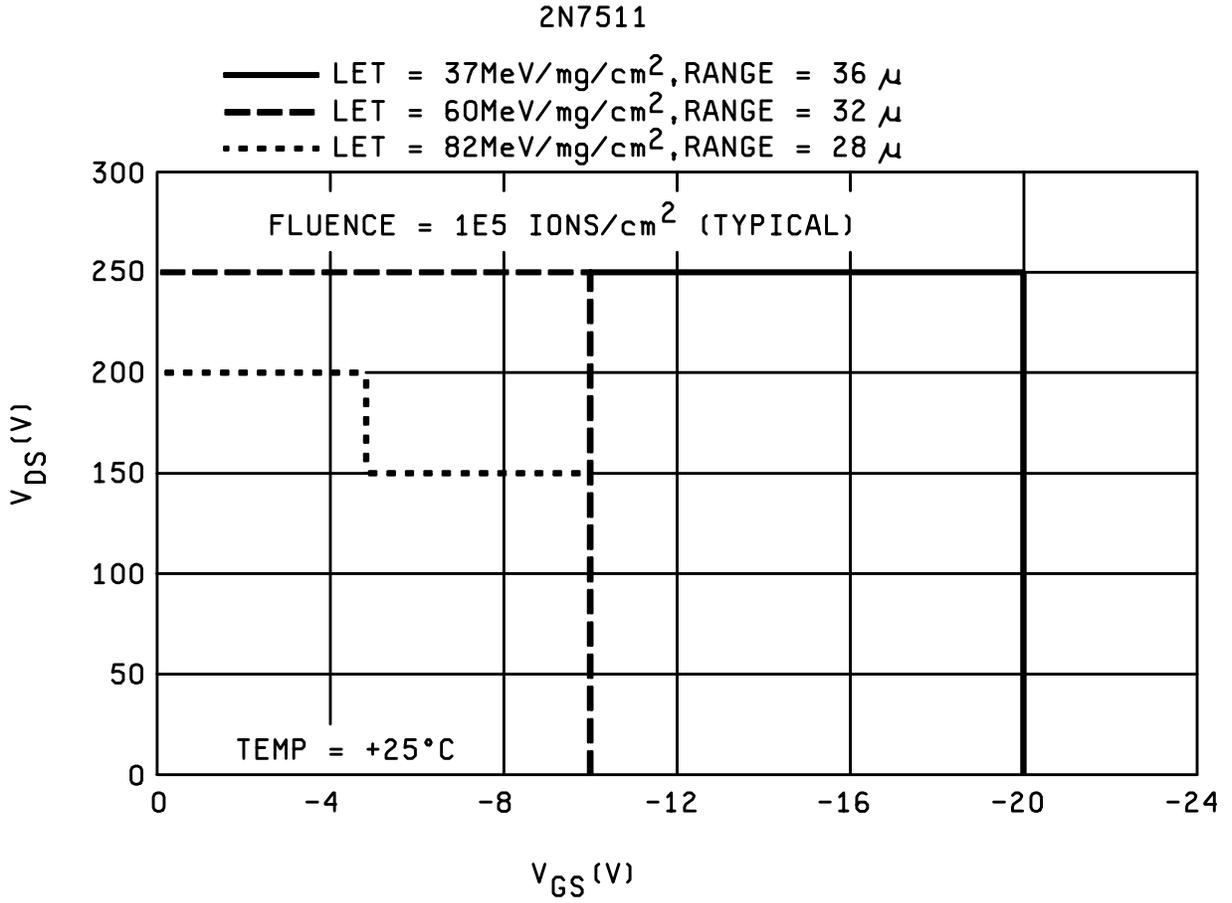
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\* FIGURE 5. Single event effects safe operating area graphs.



\* FIGURE 5. Single event effects safe operating area graphs – Continued.



\* FIGURE 5. Single event effects safe operating area graphs – Continued.

5. PACKAGING

\* 5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

\* 6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- d. Product assurance level and type designator.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail [vqe.chief@dla.mil](mailto:vqe.chief@dla.mil).

\* 6.4 Substitution information. Devices covered by this specification are substitutable for the manufacturer's and user's Part or Identifying Number (PIN). This information in no way implies that manufacturer's PINs are substitutable for the military PIN.

Generic P/N	Military P/N
FSGJ160 FSGJ260 FSGJ264	2N7509 2N7510 2N7511

\* 6.5 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:

Army - CR  
Navy - EC  
Air Force - 11  
NASA - NA  
DLA - CC

Preparing activity:  
DLA - CC

(Project 5961-2862)

Review activities:

Army - MI

\* NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <http://www.dodssp.daps.mil/> .